

June 2014

# **FQA28N15**

# N-Channel QFET® MOSFET 150 V, 33 A, 90 mΩ

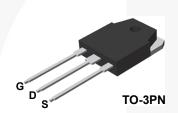
## Description

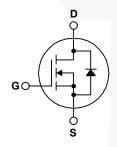
### This N-Channel enhancement mode power MOSFET is • 33 A, 150 V, $R_{DS(on)}$ = 90 m $\Omega$ (Max.) @ $V_{GS}$ = 10 V, produced using Fairchild Semiconductor's proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state • Low Gate Charge (Typ. 220 nC) resistance, and to provide superior switching performance and • Low Crss (Typ. 110 pF) high avalanche energy strength. These devices are suitable for switched mode power supplies, audio amplifier, DC motor • 100% Avalanche Tested control, and variable switching power applications.

### **Features**

- $I_D = 16.5 A$

- 175°C Maximum Junction Temperature Rating





### Absolute Maximum Ratings T<sub>C</sub> = 25°C unless otherwise noted.

Symbol	Parameter		FQA28N15	Unit	
$V_{DSS}$	Drain-Source Voltage		150	V	
I <sub>D</sub>	Drain Current - Continuous (T <sub>C</sub> = 25°C)		33	Α	
	- Continuous (T <sub>C</sub> = 100°C)		23.3	Α	
I <sub>DM</sub>	Drain Current - Pulsed	Note 1)	132	А	
V <sub>GSS</sub>	Gate-Source Voltage		± 25	V	
E <sub>AS</sub>	Single Pulsed Avalanche Energy (Note 2)		300	mJ	
I <sub>AR</sub>	Avalanche Current (Note 1)		33	Α	
E <sub>AR</sub>	Repetitive Avalanche Energy (Note 1)		22.7	mJ	
dv/dt	Peak Diode Recovery dv/dt (Note 3)		5.5	V/ns	
$P_{D}$	Power Dissipation (T <sub>C</sub> = 25°C)		227	W	
	- Derate above 25°C		1.52	W/°C	
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Temperature Range		-55 to +175	°C	
T <sub>L</sub>	Maximum lead temperature for soldering, 1/8" from case for 5 seconds.		300	°C	

### **Thermal Characteristics**

Symbol	Parameter	FQA28N15	Unit	
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case, Max.	0.66	°C/W	
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient, Max.	40	°C/W	

# **Package Marking and Ordering Information**

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FQA28N15	FQA28N15	TO-3PN	Tube	N/A	N/A	30 units

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
Off Cha	aracteristics					
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$				V
ΔBV <sub>DSS</sub> / ΔT <sub>J</sub>	Breakdown Voltage Temperature Coefficient	I <sub>D</sub> = 250 μA, Referenced to 25°C		0.17		V/°C
I <sub>DSS</sub>	Zana Oata Valtana Basin Ourset	V <sub>DS</sub> = 150 V, V <sub>GS</sub> = 0 V			1	μΑ
	Zero Gate Voltage Drain Current	V <sub>DS</sub> = 120 V, T <sub>C</sub> = 150°C			10	μΑ
I <sub>GSSF</sub>	Gate-Body Leakage Current, Forward	V <sub>GS</sub> = 25 V, V <sub>DS</sub> = 0 V			100	nA
I <sub>GSSR</sub>	Gate-Body Leakage Current, Reverse	V <sub>GS</sub> = -25 V, V <sub>DS</sub> = 0 V			-100	nA
On Cha	racteristics					
V <sub>GS(th)</sub>	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	2.0		4.0	V
R <sub>DS(on)</sub>	Static Drain-Source On-Resistance	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 16.5 A		0.067	0.09	Ω
9 <sub>FS</sub>	Forward Transconductance	V <sub>DS</sub> = 40 V, I <sub>D</sub> = 16.5 A		20		S
Dynam	ic Characteristics					
C <sub>iss</sub>	Input Capacitance	$V_{DS} = 25 \text{ V}, V_{GS} = 0 \text{ V},$		1250	1600	pF
C <sub>oss</sub>	Output Capacitance	f = 1.0 MHz		260	340	pF
C <sub>rss</sub>	Reverse Transfer Capacitance			50	65	pF
Switchi	ing Characteristics					
t <sub>d(on)</sub>	Turn-On Delay Time	V <sub>DD</sub> = 75 V, I <sub>D</sub> = 28 A,		17	45	ns
t <sub>r</sub>	Turn-On Rise Time	$R_G = 25 \Omega$		180	370	ns
t <sub>d(off)</sub>	Turn-Off Delay Time	- 1.6 2022		100	210	ns
t <sub>f</sub>	Turn-Off Fall Time	(Note 4)		115	240	ns
Qg	Total Gate Charge	V <sub>DS</sub> = 120 V, I <sub>D</sub> = 28 A,		40	52	nC
Q <sub>gs</sub>	Gate-Source Charge	V <sub>GS</sub> = 10 V (Note 4)		7.9		nC
Q <sub>gd</sub>	Gate-Drain Charge			20		nC
Drain-S	Source Diode Characteristics a	nd Maximum Ratings				
I <sub>S</sub>	Maximum Continuous Drain-Source Diode Forward Current				33	Α
I <sub>SM</sub>	Maximum Pulsed Drain-Source Diode Forward Current				132	Α
V <sub>SD</sub>	Drain-Source Diode Forward Voltage	V <sub>GS</sub> = 0 V, I <sub>S</sub> = 33 A			1.5	V
t <sub>rr</sub>	Reverse Recovery Time	V <sub>GS</sub> = 0 V, I <sub>S</sub> = 28 A,		100	/	ns
Q <sub>rr</sub>	Reverse Recovery Charge	dl <sub>F</sub> / dt = 100 A/μs		0.4		μС

**Notes:**1. Repetitive rating : pulse-width limited by maximum junction temperature.
2. L = 0.46 mH,  $I_{AS}$  = 33 A,  $V_{DD}$  = 25 V,  $R_{G}$  = 25  $\Omega$ , starting  $T_{J}$  = 25°C.
3.  $I_{SD} \le 28$  A, di/dt  $\le 300$  A/us,  $V_{DD} \le BV_{DSS}$ , starting  $T_{J}$  = 25°C.
4. Essentially independent of operating temperature.

# **Typical Characteristics**

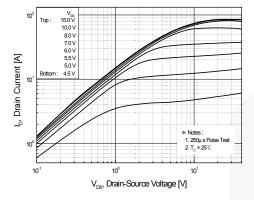


Figure 1. On-Region Characteristics

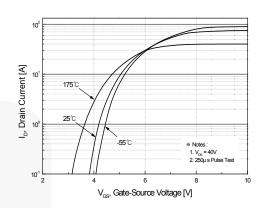


Figure 2. Transfer Characteristics

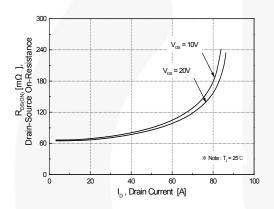


Figure 3. On-Resistance Variation vs.

Drain Current and Gate Voltage

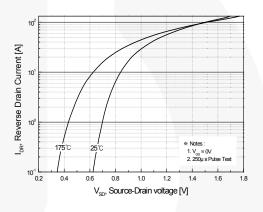


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

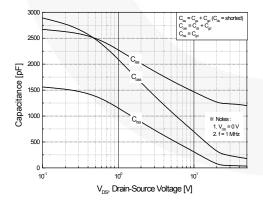


Figure 5. Capacitance Characteristics

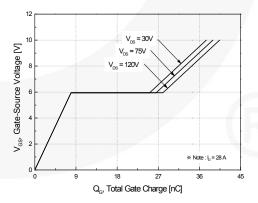


Figure 6. Gate Charge Characteristics

# Drain Source Break down Voltage (Normalized) Notes: 1. V<sub>cs</sub> = 0.0 V 2. J<sub>c</sub> = 250 µA T<sub>J</sub>, Junction Temperature [°C]

Typical Characteristics (Continued)

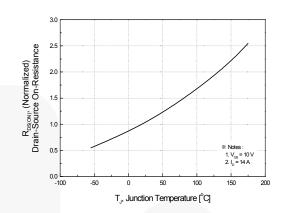
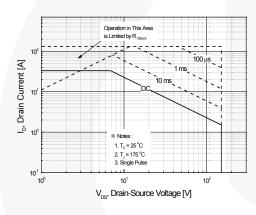


Figure 7. Breakdown Voltage Variation vs. Temperature

Figure 8. On-Resistance Variation vs. Temperature



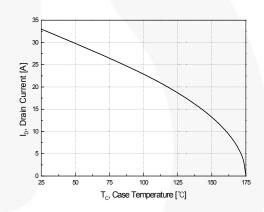


Figure 9. Maximum Safe Operating Area

Figure 10. Maximum Drain Current vs. Case Temperature

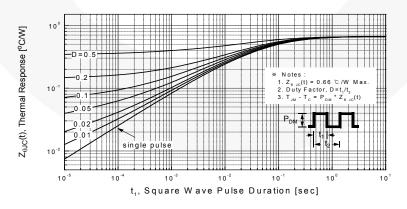


Figure 11. Transient Thermal Response Curve

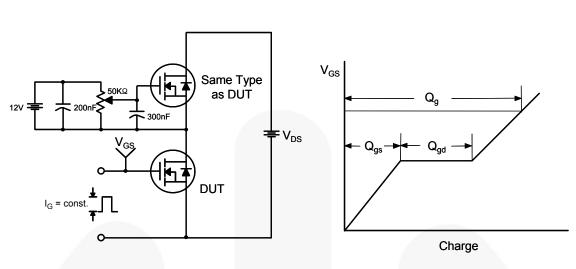


Figure 12. Gate Charge Test Circuit & Waveform

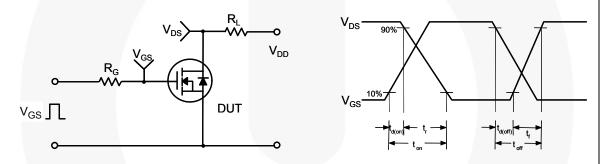


Figure 13. Resistive Switching Test Circuit & Waveforms

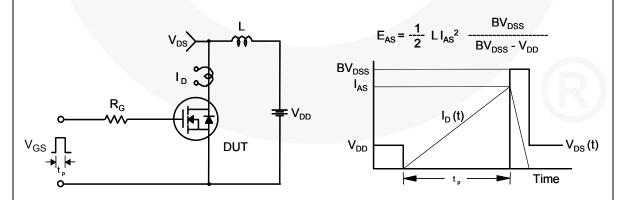
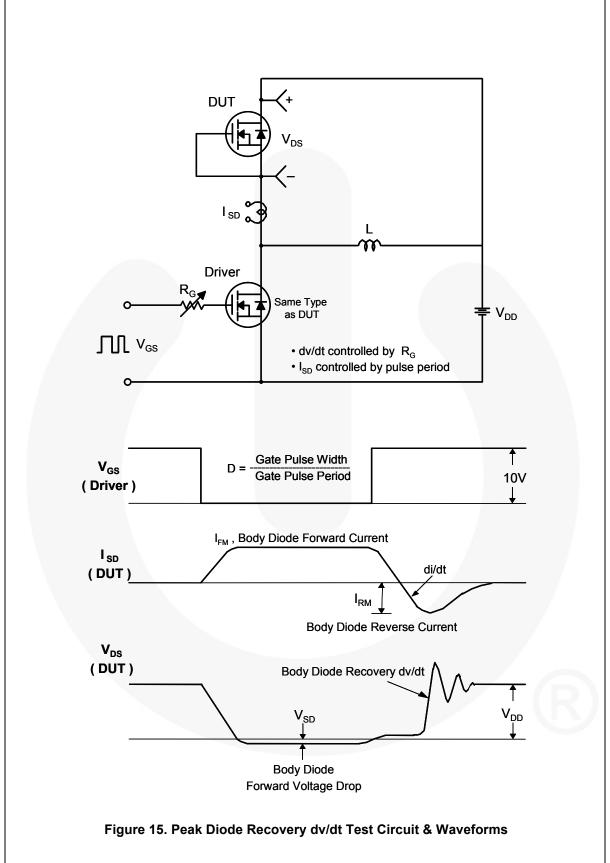
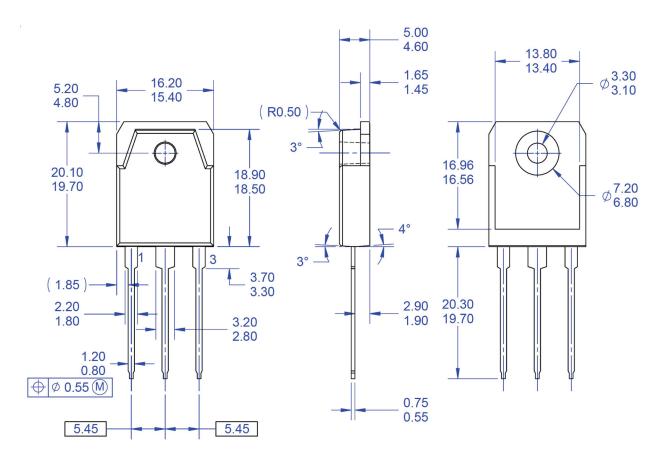
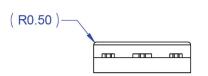


Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms



### **Mechanical Dimensions**





### NOTES: UNLESS OTHERWISE SPECIFIED

- A) THIS PACKAGE CONFORMS TO EIAJ SC-65 PACKAGING STANDARD.
   B) ALL DIMENSIONS ARE IN MILLIMETERS.
- DIMENSION AND TOLERANCING PER ASME14.5-2009.
- D) DIMENSIONS ARE EXCLUSSIVE OF BURRS, MOLD FLASH, AND TIE BAR EXTRUSSIONS. DRAWING FILE NAME: TO3PN03AREV1.
- FAIRCHILD SEMICONDUCTOR.

### Figure 16. TO3PN, 3-Lead, Plastic, EIAJ SC-65

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